removing the conductive material and the sacrificial layer using a chemical mechanical polishing process adapted to remove the conductive material and the sacrificial layer wherein the shield layer is more resistant to planarization by the chemical mechanical polishing process than the sacrificial layer;

selecting an etchant for use with the chemical mechanical polishing process to facilitate removal of the sacrificial layer, and wherein the shield layer is selected to be resistant to the selected etchant; and

detecting when the chemical mechanical polishing process has removed the sacrificial layer.

57. (New) The method of Claim 56, wherein the shield layer is formed of a material having a different hardness than the sacrificial layer and wherein detecting when the chemical mechanical polishing process has removed the sacrificial layer comprises detecting the transition between when the chemical mechanical polishing process is interacting with the sacrificial layer and the shield layer.

58. (New) The method of Claim 57, wherein the step of detecting when the chemical mechanical polishing process has removed the sacrificial layer comprises sensing the current being drawn by a motor inducing relative movement between a polishing pad and the wafer and sensing when the current drawn by the motor indicates that the pad is in contact with the shield layer.

59. (New) The method of Claim 58, wherein forming the shield layer comprises forming a dielectric antireflective coating (DARC) layer on a BPSG dielectric layer.

60. (New) The method of Claim 56, wherein the shield layer is comprised of a Nitride layer positioned on the dielectric layer.

61. (New) The method of Claim 60, wherein the sacrificial layer is comprised of a BPSG Oxide layer formed on the Nitride layer.